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FORM PTO - 1449 SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT				ATTY DOCKET NO.: ASC-025DV1C1 APPLICANT(S): Cheng <i>et al.</i> SERIAL NO.: 10/802,185 FILING DATE: March 17, 2004 GROUP: 2813					
									
U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
CAT	A236	4,969,031	11/00/1990	Kobayashi <i>et al.</i>					
CAT	A237	5,439,843	08/08/1995	Sakaguchi <i>et al.</i>					
CAT	A238	5,548,128	08/20/1996	Soref <i>et al.</i>					
CAT	A239	5,607,876	03/04/1997	Biegelsen <i>et al.</i>					
CAT	A240	6,489,639	12/03/2002	Hoke <i>et al.</i>					
CAT	A241	6,591,321	07/08/2003	Arimilli <i>et al.</i>			11/09/1999		
CAT	A242	6,597,016	07/22/2003	Yuki <i>et al.</i>			01/13/2000		
CAT	A243	6,646,322	11/11/2003	Fitzgerald			07/16/2001		
CAT	A244	6,674,150	01/06/2004	Takagi <i>et al.</i>			04/23/2002		
CAT	A245	6,677,192	01/13/2004	Fitzgerald			07/16/2001		
CAT	A246	6,703,144	03/09/2004	Fitzgerald			03/18/2003		
CAT	A247	6,703,688	03/09/2004	Fitzgerald			7/16/2001		
CAT	A248	6,737,670	05/18/2004	Cheng <i>et al.</i>			03/07/2003		
CAT	A249	6,750,130	01/07/2001	Fitzgerald			01/07/2001		
CAT	A250	2002/0084000	07/04/2002	Fitzgerald			12/17/2001		
CAT	A251	2003/0215990	11/20/2003	Fitzgerald <i>et al.</i>			03/14/2003		
CAT	A252	2004/0075149	04/22/2004	Fitzgerald <i>et al.</i>			07/23/2003		
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
CAT	B45	61-141116	06/28/1986	JP				N	Y (abstract only)
CAT	B46	2-210816	08/22/1990	JP				N	Y (abstract only)
CAT	B47	3-036717	02/18/1991	JP				N	Y
EXAMINER Craig A. Thompson					DATE CONSIDERED 12/28/04				

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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT				APPLICANT(S): Cheng <i>et al.</i>					
				SERIAL NO.: 10/802,185					
				FILING DATE: March 17, 2004					
				GROUP: 2813					
U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
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FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
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/		/			/		/		/
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
CA	C99	Grillot <i>et al.</i> , "Acceptor diffusion and segregation in $(\text{Al}_x\text{Ga}_{1-x})_{0.5}\text{In}_{0.5}\text{P}$ heterostructures," <u>Journal of Applied Physics</u> , Vol. 91, No. 8 (2002), pp. 4891-4899.							
CA	C100	Halsall <i>et al.</i> , "Electron diffraction and Raman studies of the effect of substrate misorientation on ordering in the AlGaInP system," <u>Journal of Applied Physics</u> , Vol. 85, No. 1 (1999), pp. 199-202.							
CA	C101	Hsu <i>et al.</i> , "Surface morphology of related $\text{Ge}_x\text{Si}_{1-x}$ films," <u>Appl. Phys. Lett.</u> , Vol. 61, No. 11 (1992), pp. 1293-1295							
EXAMINER		Craig A. Thompson			DATE CONSIDERED		12/28/04		

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APPLICANTS: Cheng *et al.*

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U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CA	A235	5,572,043	11/5/1996	Shimizu <i>et al.</i>			05/15/1995

FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)

OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT. OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)

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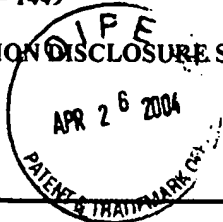
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ATTY DOCKET NO.: ASC-025DVC1

APPLICANTS: Cheng et al.

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GROUP: Not yet assigned 2813

U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CAT	A1	4,010,045	03/01/1977	Ruehrwein			
CAT	A2	4,704,302	11/03/1987	Bruehl et al.			
CAT	A3	4,710,788	12/01/1987	Dämbkes et al.			
CAT	A4	4,987,462	01/22/1991	Kim et al.			
CAT	A5	4,990,979	02/05/1991	Otto			
CAT	A6	4,997,776	03/05/1991	Haramie et al.			
CAT	A7	5,013,681	05/07/1991	Godbey et al.			
CAT	A8	5,155,571	10/13/1992	Wang et al.			
CAT	A9	5,166,084	11/24/1992	Pfiester			
CAT	A10	5,177,583	01/05/1993	Endo et al.			
CAT	A11	5,202,284	04/13/1993	Kamins et al.			
CAT	A12	5,207,864	05/04/1993	Bhat et al.			
CAT	A13	5,208,182	05/04/1993	Narayan et al.			
CAT	A14	5,212,110	05/18/1993	Pfiester et al.			
CAT	A15	5,221,413	06/22/1993	Brasen et al.			
CAT	A16	5,240,876 A	08/31/1993	Gaul et al.			
CAT	A17	5,241,197	08/31/1993	Murakami et al.			
CAT	A18	5,250,445	10/05/1993	Bean et al.			
CAT	A19	5,285,086	02/08/1994	Fitzgerald			
CAT	A20	5,291,439	03/01/1994	Kauffmann et al.			
CAT	A21	5,298,452	03/29/1994	Meyerson			
CAT	A22	5,310,451	05/10/1994	Tejwani et al.			
CAT	A23	5,316,958	05/31/1994	Meyerson			
CAT	A24	5,346,848	09/13/1994	Gruppen-Shemansky et al.			
CAT	A25	5,374,564	12/20/1994	Bruehl			
CAT	A26	5,399,522	03/21/1995	Ohori			
CAT	A27	5,413,679	05/09/1995	Godbey			

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U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CAT	A28	5,424,243	06/13/1995	Takasaki			
CAT	A29	5,426,069	06/20/1995	Selvakumar <i>et al.</i>			
CAT	A30	5,426,316	06/20/1995	Mohammad			
CAT	A31	5,442,205	08/15/1995	Brasen <i>et al.</i>			
CAT	A32	5,461,243	10/24/1995	Ek <i>et al.</i>			
CAT	A33	5,461,250	10/24/1995	Burghartz <i>et al.</i>			
CAT	A34	5,462,883	10/31/1995	Dennard <i>et al.</i>			
CAT	A35	5,476,813	12/19/1995	Naruse			
CAT	A36	5,479,033	12/26/1995	Baca <i>et al.</i>			
CAT	A37	5,484,664	01/16/1996	Kitahara <i>et al.</i>			
CAT	A38	5,523,243	06/04/1996	Mohammad			
CAT	A39	5,523,592	06/04/1996	Nakagawa <i>et al.</i>			
CAT	A40	5,534,713	07/09/1996	Ismail <i>et al.</i>			
CAT	A41	5,536,361	07/16/1996	Kondo <i>et al.</i>			
CAT	A42	5,540,785	07/30/1996	Dennard <i>et al.</i>			
CAT	A43	5,596,527	01/21/1997	Tomioka <i>et al.</i>			
CAT	A44	5,617,351	04/01/1997	Bertin <i>et al.</i>			
CAT	A45	5,630,905	05/20/1997	Lynch <i>et al.</i>			
CAT	A46	5,659,187	08/19/1997	Legoues <i>et al.</i>			
CAT	A47	5,683,934	11/04/1997	Candelaria			
CAT	A48	5,698,869	12/16/1997	Yoshimi <i>et al.</i>			
CAT	A49	5,714,777	02/03/1998	Ismail <i>et al.</i>			
CAT	A50	5,728,623	03/17/1998	Mori			
CAT	A51	5,739,567	04/14/1998	Wong			
CAT	A52	5,759,898	06/02/1998	Ek <i>et al.</i>			
CAT	A53	5,777,347	07/07/1998	Bartelink			
CAT	A54	5,786,612	07/28/1998	Otani <i>et al.</i>			

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				GROUP: Not yet assigned 2813			
U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CAT	A55	5,786,614	07/28/1998	Chuang <i>et al.</i>			
CAT	A56	5,792,679	08/11/1998	Nakato			
CAT	A57	5,808,344	09/15/1998	Ismail <i>et al.</i>			
CAT	A58	5,847,419	12/08/1998	Imai <i>et al.</i>			
CAT	A59	5,863,830	01/26/1999	Bruel <i>et al.</i>			
CAT	A60	5,877,070	03/02/1999	Goesele <i>et al.</i>			
CAT	A61	5,882,987	03/16/1999	Srikrishnan			
CAT	A62	5,891,769	04/06/1999	Hong <i>et al.</i>			
CAT	A63	5,906,708	05/25/1999	Robinson <i>et al.</i>			
CAT	A64	5,906,951	05/25/1999	Chu <i>et al.</i>			
CAT	A65	5,912,479	06/15/1999	Mori <i>et al.</i>			
CAT	A66	5,943,560	08/24/1999	Chang <i>et al.</i>			
CAT	A67	5,963,817	10/05/1999	Chu <i>et al.</i>			
CAT	A68	5,966,622	10/12/1999	Levine <i>et al.</i>			
CAT	A69	5,993,677	11/30/1999	Biasse <i>et al.</i>			
CAT	A70	5,998,807	12/07/1999	Lustig <i>et al.</i>			
CAT	A71	6,013,134	01/11/2000	Chu <i>et al.</i>			
CAT	A72	6,013,563	01/11/2000	Henley <i>et al.</i>			
CAT	A73	6,020,252	02/01/2000	Aspar <i>et al.</i>			
CAT	A74	6,033,974	03/07/2000	Henley <i>et al.</i>			
CAT	A75	6,033,995	03/07/2000	Muller			
CAT	A76	6,058,044	05/02/2000	Sugiura <i>et al.</i>			
CAT	A77	6,059,895	05/09/2000	Chu <i>et al.</i>			
CAT	A78	6,074,919	06/13/2000	Gardner <i>et al.</i>			
CAT	A79	6,096,590	08/01/2000	Chan <i>et al.</i>			
CAT	A80	6,103,559	08/15/2000	Gardner <i>et al.</i>			
CAT	A81	6,103,597	08/15/2000	Aspar <i>et al.</i>			
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GROUP: Not yet assigned 2113

U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CAT	A82	6,103,599	08/15/2000	Henley et al.			
CAT	A83	6,107,653	08/22/2000	Fitzgerald			
CAT	A84	6,111,267	08/29/2000	Fischer et al.			
CAT	A85	6,117,750	09/12/2000	Bensahel et al.			
CAT	A86	6,130,453	10/10/2000	Mei, et al.			
CAT	A87	6,133,799	10/17/2000	Favors Jr., et al.			
CAT	A88	6,140,687	10/31/2000	Shimomura et al.			
CAT	A89	6,143,636	11/07/2000	Forbes et al.			
CAT	A90	6,153,495	11/28/2000	Kub et al.			
CAT	A91	6,154,475	11/28/2000	Soref et al.			
CAT	A92	6,160,303	12/12/2000	Fattaruso			
CAT	A93	6,162,688	12/19/2000	Gardner et al.			
CAT	A94	6,162,705	12/19/2000	Henley et al.			
CAT	A95	6,184,111	02/06/2001	Henley et al.			
CAT	A96	6,190,998 B1	02/20/2001	Bruel et al.			
CAT	A97	6,191,007	02/20/2001	Matsui et al.			
CAT	A98	6,191,432	02/20/2001	Sugiyama et al.			
CAT	A99	6,194,722	02/27/2001	Howe et al.			
CAT	A100	6,204,529	03/20/2001	Lung, et al.			
CAT	A101	6,207,977	03/27/2001	Augusto			
CAT	A102	6,210,988	04/03/2001	Howe et al.			
CAT	A103	6,218,677	04/17/2001	Broekaert			
CAT	A104	6,225,192 B1	05/01/2001	Aspar et al.			
CAT	A105	6,232,138	05/15/2001	Fitzgerald et al.			
CAT	A106	6,235,567	05/22/2001	Huang			
CAT	A107	6,242,324	06/05/2001	Kub et al.			
CAT	A108	6,249,022	06/19/2001	Lin, et al.			

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FORM PTO - 1449				ATTY DOCKET NO.: ASC-025DVC1			
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U.S. PATENT DOCUMENTS							
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CAT	A109	6,251,751 B1	06/26/2001	Chu <i>et al.</i>			
CAT	A110	6,251,755	06/26/2001	Furukawa <i>et al.</i>			
CAT	A111	6,261,929	07/17/2001	Gehrke <i>et al.</i>			
CAT	A112	6,266,278	07/24/2001	Harari, <i>et al.</i>			
CAT	A113	6,271,551	08/07/2001	Schmitz <i>et al.</i>			
CAT	A114	6,271,726	08/07/2001	Fransis <i>et al.</i>			
CAT	A115	6,290,804 B1	09/18/2001	Henley <i>et al.</i>			02/20/1998
CAT	A116	6,291,321	09/18/2001	Fitzgerald			03/09/1999
CAT	A117	6,303,468 B1	10/16/2001	Aspar <i>et al.</i>			10/16/2001
CAT	A118	6,313,016	11/06/2001	Kibbel <i>et al.</i>			12/22/1999
CAT	A119	6,316,301	11/13/2001	Kant			03/08/200
CAT	A120	6,323,108	11/27/2001	Kub <i>et al.</i>			07/27/1999
CAT	A121	6,326,667 B1	12/04/2001	Sugiyama <i>et al.</i>			09/08/2000
CAT	A122	6,329,063	12/11/2001	Lo <i>et al.</i>			12/11/1998
CAT	A123	6,335,546	01/01/2002	Tsuda <i>et al.</i>			07/30/1999
CAT	A124	6,339,232	01/15/2002	Takagi			09/20/1999
CAT	A125	6,344,417 B1	02/05/2002	Usenko			08/08/2000
CAT	A126	6,346,459 B1	02/12/2002	Usenko <i>et al.</i>			02/02/2000
CAT	A127	6,350,993	02/26/2002	Chu <i>et al.</i>			03/12/1999
CAT	A128	6,352,909 B1	03/05/2002	Usenko			05/26/2000
CAT	A129	6,355,493 B1	03/12/2002	Usenko			06/30/2000
CAT	A130	6,368,733	04/09/2002	Nishinaga			08/05/1999
CAT	A131	6,368,938 B1	04/09/2002	Usenko			06/07/2000
CAT	A132	6,369,438 B1	04/09/2002	Sugiyama <i>et al.</i>			12/22/2000
CAT	A133	6,372,356	04/16/2002	Thornton <i>et al.</i>			04/28/2000
CAT	A134	6,372,593 B1	04/16/2002	Hattori <i>et al.</i>			07/19/2000
CAT	A135	6,372,609 B1	04/16/2002	Aga <i>et al.</i>			10/08/1999
EXAMINER <i>Craig A. Harper</i>				DATE CONSIDERED <i>12/28/04</i>			

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INFORMATION DISCLOSURE STATEMENT

ATTY DOCKET NO.: ASC-025DVC1

APPLICANTS: Cheng *et al.*

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U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CAT	A136	6,387,829 B1	05/14/2002	Usenko et al.			04/06/2000
CAT	A137	6,391,740 B1	05/21/2002	Cheung et al.			04/28/1999
CAT	A138	6,399,970	06/04/2002	Kubo et al.			09/19/1997
CAT	A139	6,403,975	06/11/2002	Brunner et al.			04/08/1997
CAT	A140	6,407,406	06/18/2002	Tezuka			06/29/1999
CAT	A141	6,410,371 B1	06/25/2002	Yu et al.			02/26/2001
CAT	A142	6,425,951	07/30/2002	Chu et al.			08/06/1999
CAT	A143	6,429,061	08/06/2002	Rim			07/26/2000
CAT	A144	6,445,016 B1	09/03/2002	An et al.			02/28/2001
CAT	A145	6,448,152 B1	09/10/2002	Henley et al.			07/16/2001
CAT	A146	6,455,397 B1	09/24/2002	Belford			11/09/2000
CAT	A147	6,458,672 B1	10/01/2002	Henley et al.			11/02/2000
CAT	A148	6,475,072 B1	11/05/2002	Canaperi et al.			09/29/2000
CAT	A149	6,514,836 B2	02/04/2003	Belford			06/04/2001
CAT	A150	6,515,335 B1	02/04/2003	Christiansen et al.			01/04/2002
CAT	A151	6,521,041	02/18/2003	Wu et al.			04/09/1999
CAT	A152	6,524,935 B1	02/25/2003	Canaperi et al.			09/29/2000
CAT	A153	6,534,381 B2	03/18/2003	Cheung et al.			01/04/2000
CAT	A154	6,555,839	04/29/2003	Fitzgerald et al.			05/16/2001
CAT	A155	6,573,126	06/03/2003	Cheng et al.			08/10/2001
CAT	A156	6,583,015	06/24/2003	Fitzgerald et al.			08/06/2001
CAT	A157	6,583,437 B2	06/24/2003	Mizuno et al.			03/19/2001
CAT	A158	6,593,191	07/15/2003	Fitzgerald			05/16/2001
CAT	A159	6,593,625 B2	07/15/2003	Christiansen et al.			04/03/2002
CAT	A160	6,596,610 B1	07/22/2003	Kuwabara et al.			11/27/2000
CAT	A161	6,602,613	08/05/2003	Rim			01/17/2001
CAT	A162	6,603,156	08/05/2003	Fitzgerald			03/31/2001

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FORM PTO - 1449				ATTY DOCKET NO.: ASC-025DVC1			
INFORMATION DISCLOSURE STATEMENT				APPLICANTS: Cheng <i>et al.</i>			
				SERIAL NO.: 10/802,185			
				FILING DATE: March 17, 2004			
				GROUP: Not yet assigned - 2813			
U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CAI	A163	6,607,948 B1	08/19/2003	Sugiyama <i>et al.</i>			08/24/2001
CAI	A164	6,624,047 B1	09/23/2003	Sakaguchi <i>et al.</i>			02/01/2000
CAI	A165	6,624,478 B2	09/23/2003	Anderson <i>et al.</i>			01/30/2002
CAI	A166	6,632,724 B2	10/14/2003	Henley <i>et al.</i>			01/13/2000
CAI	A167	6,635,909 B2	10/21/2003	Clark <i>et al.</i>			03/19/2002
CAI	A168	6,645,831 B1	11/11/2003	Shaheen <i>et al.</i>			05/07/2002
CAI	A169	6,649,492 B2	11/18/2003	Chu <i>et al.</i>			02/11/2002
CAI	A170	6,656,271 B2	12/02/2003	Yonchara <i>et al.</i>			12/03/1999
CAI	A171	6,664,169 B1	12/16/2003	Iwasaki <i>et al.</i>			06/05/2000
CAI	A172	6,677,183 B2	01/13/2004	Sakaguchi <i>et al.</i>			01/31/2002
CAI	A173	6,680,240 B1	01/20/2004	Maszara			06/25/2002
CAI	A174	6,680,260 B2	01/20/2004	Akiyama <i>et al.</i>			09/17/2002
CAI	A175	6,690,043 B1	02/10/2004	Usuda <i>et al.</i>			11/22/2000
CAI	A176	6,706,614 B1	03/16/2004	An <i>et al.</i>			05/15/2002
CAI	A177	6,706,618 B2	03/16/2004	Takisawa <i>et al.</i>			07/29/2002
CAI	A178	6,707,106 B1	03/16/2004	Wristers <i>et al.</i>			10/18/2002
CAI	A179	6,709,903 B2	03/23/2004	Christiansen <i>et al.</i>			04/30/2003
CAI	A180	6,709,909 B2	03/23/2004	Mizuno <i>et al.</i>			05/19/2003
CAI	A181	6,713,326 B2	03/30/2004	Cheng <i>et al.</i>			03/04/2003
CAI	A182	2001/0003364	06/14/2001	Sugawara <i>et al.</i>			12/08/2000
CAI	A183	2001/0007789 A1	07/12/2001	Aspar <i>et al.</i>			02/26/2001
CAI	A184	2002/0043660	04/18/2002	Yamazaki <i>et al.</i>			06/25/2001
CAI	A185	2002/052084	05/02/2002	Fitzgerald			05/16/2001
CAI	A186	2002/096717	07/25/2002	Chu <i>et al.</i>			01/25/2001
CAI	A187	2002/0100942	08/01/2002	Fitzgerald <i>et al.</i>			08/01/2002
CAI	A188	2002/0123167	09/05/2002	Fitzgerald			07/16/2001
CAI	A189	2002/0123183	09/05/2002	Fitzgerald			07/16/2001
EXAMINER <i>Craig A. Johnson</i>				DATE CONSIDERED <i>12/28/04</i>			

FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT				ATTY DOCKET NO.: ASC-025DVC1 APPLICANTS: Cheng <i>et al.</i> SERIAL NO.: 10/802,185 FILING DATE: March 17, 2004 GROUP: Not yet assigned 2813			
U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CAI	A190	2002/0123197	09/05/2002	Fitzgerald et al.			06/19/2001
CAI	A191	2002/0125471	09/12/2002	Fitzgerald et al.			12/04/2001
CAI	A192	2002/0125497	09/12/2002	Fitzgerald			07/16/2001
CAI	A193	2002/0168864	11/14/2002	Cheng et al.			04/04/2002
CAI	A194	2003/0003679	01/02/2003	Doyle et al.			06/29/2001
CAI	A195	2003/0013305 A1	01/16/2003	Sugii et al.			6/17/2002
CAI	A196	2003/0013323	01/16/2003	Hammond et al.			6/14/2002
CAI	A197	2003/0025131	02/06/2003	Lee et al.			08/02/2002
CAI	A198	2003/0034529	02/20/2003	Fitzgerald et al.			10/08/2002
CAI	A199	2003/0057439	03/27/2003	Fitzgerald			08/09/2002
CAI	A200	2003/0077867	04/04/2003	Fitzgerald			07/16/2001
CAI	A201	2003/0102498	06/05/2003	Braithwaite et al.			09/24/2002
CAI	A202	2003/0119280 A1	06/26/2003	Lee et al.			12/02/2002
CAI	A203	2003/0127646 A1	07/10/2003	Christiansen et al.			12/18/2002
CAI	A204	2003/0139000 A1	07/24/2003	Bedell et al.			01/23/2002
CAI	A205	2003/0157787 A1	08/21/2003	Murthy et al.			02/21/2002
CAI	A206	2003/0160300 A1	08/28/2003	Takenaka et al.			02/24/2003
CAI	A207	2003/0168654 A1	09/11/2003	Cheng et al.			03/07/2003
CAI	A208	2003/0178681 A1	09/25/2003	Clark et al.			04/02/2003
CAI	A209	2003/0189229 A1	10/09/2003	Mouli			04/05/2002
CAI	A210	2003/0199126 A1	10/23/2003	Chu et al.			04/23/2002
CAI	A211	2003/0201458 A1	10/30/2003	Clark et al.			05/16/2003
CAI	A212	2003/0203600 A1	10/30/2003	Chu et al.			06/05/2003
CAI	A213	2003/0207127 A1	11/06/2003	Murthy et al.			05/30/2003
CAI	A214	2003/0218189 A1	11/27/2003	Christiansen et al.			11/19/2002
CAI	A215	2003/0219957 A1	11/27/2003	Kuwabara et al.			05/29/2003
CAI	A216	2003/0227036 A1	12/11/2003	Sugiyama et al.			02/21/2003
EXAMINER <i>Chris A. [Signature]</i>				DATE CONSIDERED 12/28/04			

FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT				ATTY DOCKET NO.: ASC-025DVC1 APPLICANTS: Cheng <i>et al.</i> SERIAL NO.: 10/802,185 FILING DATE: March 17, 2004 GROUP: Not yet assigned 2813					
U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
CAJ	A217	2003/0227057	12/01/2003	Lochtefeld <i>et al.</i>			10/04/2002		
CAJ	A218	2003/0230778 A1	12/18/2003	Park <i>et al.</i>			01/30/2003		
CAJ	A219	2003/0232467 A1	12/18/2003	Anderson <i>et al.</i>			05/29/2003		
CAJ	A220	2004/0005740	01/01/2004	Lochtefeld <i>et al.</i>			06/06/2003		
CAJ	A221	2004/0007724 A1	01/15/2004	Murthy <i>et al.</i>			07/12/2002		
CAJ	A222	2004/0009649 A1	01/15/2004	Kub <i>et al.</i>			05/20/2003		
CAJ	A223	2004/0012037 A1	01/22/2004	Venkatesan <i>et al.</i>			07/18/2002		
CAJ	A224	2004/0012075 A1	01/22/2004	Bedell <i>et al.</i>			07/16/2002		
CAJ	A225	2004/0014304 A1	01/22/2004	Bhattacharyya			07/18/2002		
CAJ	A226	2004/0018699 A1	01/29/2004	Boyd <i>et al.</i>			07/24/2002		
CAJ	A227	2004/0031979	02/19/2004	Lochtefeld <i>et al.</i>			06/06/2003		
CAJ	A228	2004/0031990 A1	02/19/2004	Jin <i>et al.</i>			08/16/2002		
CAJ	A229	2004/0041174 A1	03/04/2004	Okihara			03/21/2003		
CAJ	A230	2004/0041210 A1	03/04/2004	Mouli			09/02/2003		
CAJ	A231	2004/0048091 A1	03/11/2004	Sato <i>et al.</i>			09/04/2003		
CAJ	A232	2004/0048454 A1	03/11/2004	Sakaguchi			09/04/2003		
CAJ	A233	2004/0051140 A1	03/18/2004	Bhattacharyya			09/12/2002		
CAJ	A234	2004/0053477 A1	03/18/2004	Ghyselen <i>et al.</i>			07/09/2003		
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
CAJ	B1	41 01 167	07/23/1992	DE				No	No
CAJ	B2	0 514 018	11/19/1992	EP				No	Yes
CAJ	B3	0 587 520	03/16/1994	EP				No	Yes
CAJ	B4	0 683 522	11/22/1995	EP				No	Yes
CAJ	B5	0 828 296	03/11/1998	EP				No	Yes
CAJ	B6	0 829 908	03/18/1998	EP				No	Yes
CAJ	B7	0 838 858	04/29/1998	EP				No	No
EXAMINER <i>Chen a. JH</i>				DATE CONSIDERED <i>12/28/04</i>					

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FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLAS S	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
LAT	B8	1 020 900	07/19/2000	EP				No	Yes
LAT	B9	1 174 928	01/23/2002	EP				No	Yes
LAT	B10	2 342 777	04/19/2000	GB				Yes	Yes
AT	B11	4-307974	10/30/1992	JP				No	No
LAT	B12	5-166724	07/03/1993	JP				No	Abstract Only
LAT	B13	6-177046	06/24/1994	JP				No	Abstract Only
LAT	B14	7-106446	04/21/1995	JP				No	No
LAT	B15	7-240372	09/12/1995	JP				No	Abstract Only
LAT	B16	10-270685	10/09/1998	JP				No	Yes
AT	B17	11-233744	08/27/1999	JP				No	No
AT	B18	2000-021783	01/21/2000	JP				No	Yes
AT	B19	2000-31491	01/28/2000	JP				No	No
AT	B20	2001319935	05/11/2000	JP				Yes	Yes
AT	B21	2002-076334	03/15/2002	JP				No	Yes
AT	B22	2002-164520	06/07/2002	JP				No	Yes
AT	B23	2002-289533	10/04/2002	JP				No	Yes
AT	B24	WO 98/59365	12/30/1998	PCT				No	Yes
AT	B25	WO 99/53539	10/21/1999	PCT				No	Yes
AT	B26	WO 00/48239	08/17/2000	PCT				No	Yes
AT	B27	WO 01/54202	07/26/2001	PCT				No	Yes
AT	B28	WO 01/99169A2	12/27/2001	PCT				No	Yes
AT	B29	WO 02/15244 A2	02/21/2002	PCT				No	Yes
AT	B30	WO 02/27783 A1	04/04/2002	PCT				No	Yes
AT	B31	WO 02/071495A1	09/12/2002	PCT				No	Yes
EXAMINER Craig A. 20				DATE CONSIDERED 12/28/04					

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FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
CAJ	B32	WO 02/082514 A1	10/17/2002	PCT				No	Yes
CAJ	B33	WO 00/54338	09/14/2000	WO				No	Yes
CAJ	B34	WO 01/022482	03/29/2001	WO				No	Yes
CAJ	B35	WO 01/93338	12/06/2001	WO				No	Yes
CAJ	B36	WO 02/13262	02/14/2002	WO				No	Yes
CAJ	B37	WO 02/47168	06/13/2002	WO				No	Yes
CAJ	B38	WO 02/071488	09/12/2002	WO				No	Yes
CAJ	B39	WO 02/071491	09/12/2002	WO				No	Yes
CAJ	B40	WO 04/006311 A2	01/15/2004	WO			07/09/2003		YES
CAJ	B41	WO 04/006326 A1	01/15/2004	WO			07/09/2003		YES
CAJ	B42	WO 04/006327 A2	01/15/2004	WO			07/09/2003		YES
CAJ	B43	WO 04/019403 A2	03/04/2004	WO			08/26/2003		YES
CAJ	B44	WO 04/019404 A2	03/04/2004	WO			08/26/2003		YES
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
CAJ	C1	"2 Bit/Cell EEPROM Cell Using Band to Band Tunneling for Data Read-Out," IBM Technical Disclosure Bulletin, Vol. 35, No. 4B (September 1992) pp. 136-140.							
CAJ	C2	Armstrong et al., "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," <u>IEDM Technical Digest</u> (1995) pp. 761-764.							
CAJ	C3	Armstrong, "Technology for SiGe Heterostructure-Based CMOS Devices", Ph.D Thesis, Massachusetts Institute of Technology (1999) pp. 1-154.							
CAJ	C4	Augusto et al., "Proposal for a New Process Flow for the Fabrication of Silicon-Based Complementary MOD-MOSFETs without Ion Implantation," <u>Thin Solid Films</u> , Vol. 294, No. 1-2 (1997) pp. 254-258.							
CAJ	C5	Barradas et al., "RBS analysis of MBE-grown SiGe/(001) Si heterostructures with thin, high Ge content SiGe channels for HMOS transistors," <u>Modern Physics Letters B</u> (2001) (abstract).							
EXAMINER Craig A. Zeller				DATE CONSIDERED 12/28/04					

FORM PTO - 1449		ATTY DOCKET NO.: ASC-025DVC1
INFORMATION DISCLOSURE STATEMENT		APPLICANTS: Cheng <i>et al.</i>
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OTHER ART, JOURNAL ARTICLES, ETC.		
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
CAT	C6	Borenstein et al., "A New Ultra-Hard Etch-Stop Layer for High Precision Micromachining," <u>Proceedings of the 1999 12th IEEE International Conference on Micro Electro Mechanical Systems (MEMS)</u> (January 17-21, 1999) pp. 205-210.
CAT	C7	Bouillon et al., "Search for the optimal channel architecture for 0.18/0.12 μm bulk CMOS Experimental study," <u>IEEE</u> (1996) pp. 21.2.1-21.2.4.
CAT	C8	Bruel et al., "@SMART CUT: A Promising New SOI Material Technology," <u>Proceedings 1995 IEEE International SOI Conference</u> (October 1995) pp. 178-179.
CAT	C9	Bruel, "Silicon on Insulator Material Technology," <u>Electronic Letters</u> , Vol. 13, No. 14 (July 6, 1995) pp. 1201-1202.
CAT	C10	Bufler et al., "Hole transport in strained $\text{Si}_{1-x}\text{Ge}_x$ alloys on $\text{Si}_{1-y}\text{Ge}_y$ substrates," <u>Journal of Applied Physics</u> , Vol. 84, No. 10 (November 15, 1998) pp. 5597-5602.
CAT	C11	Burghartz et al., "Microwave Inductors and Capacitors in Standard Multilevel Interconnect Silicon Technology," <u>IEEE Transactions on Microwave Theory and Techniques</u> , Vol. 44, No. 1 (January 1996) pp. 100-104.
CAT	C12	Canaperi et al., "Preparation of a relaxed Si-Ge layer on an insulator in fabricating high-speed semiconductor devices with strained epitaxial films," International Business Machines Corporation, USA (2002) (abstract).
CAT	C13	Carlin et al., "High Efficiency GaAs-on-Si Solar Cells with High Voc Using Graded GeSi Buffers," <u>IEEE</u> (2000) pp. 1006-1011
CAT	C14	Chang et al., "Selective Etching of SiGe/Si Heterostructures," <u>Journal of the Electrochemical Society</u> , No. 1 (January 1991) pp. 202-204.
CAT	C15	Cheng et al., "Electron Mobility Enhancement in Strained-Si n-MOSFETs Fabricated on SiGe-on-Insulator (SGOI) Substrates," <u>IEEE Electron Device Letters</u> , Vol. 22, No. 7 (July 2001) pp. 321-323.
CAT	C16	Cheng et al., "Relaxed Silicon-Germanium on Insulator Substrate by Layer Transfer," <u>Journal of Electronic Materials</u> , Vol. 30, No. 12 (2001) pp. L37-L39.
CAT	C17	Cullis et al., "Growth ripples upon strained SiGe epitaxial layers on Si and misfit dislocation interactions," <u>Journal of Vacuum Science and Technology A</u> , Vol. 12, No. 4 (July/August 1994) pp. 1924-1931.
CAT	C18	Currie et al., "Carrier mobilities and process stability of strained Si n- and p-MOSFETs on SiGe virtual substrates," <u>J. Vac. Sci. Technol. B</u> , Vol. 19, No. 6 (Nov/Dec 2001) pp. 2268-2279.
CAT	C19	Currie et al., "Controlling Threading Dislocation in Ge on Si Using Graded SiGe Layers and Chemical-Mechanical Polishing," vol. 72 No. 14 (April 6, 1998) pp. 1718-1720.
CAT	C20	Eaglesham et al., "Dislocation-Free Stranski-Krastanow Growth of Ge on Si(100)," <u>Physical Review Letters</u> , Vol. 64, No. 16 (April 16, 1990) pp. 1943-1946.
CAT	C21	Feijoo et al., "Epitaxial Si-Ge Etch Stop Layers with Ethylene Diamine Pyrocatechol for Bonded and Etchback Silicon-on-Insulator," <u>Journal of Electronic Materials</u> , Vol. 23, No. 6 (June 1994) pp. 493-496.
CAT	C22	Fischetti et al., "Band structure, deformation potentials, and carrier mobility in strained Si, Ge, and SiGe alloys," <u>J. Appl. Phys.</u> , Vol. 80, No. 4 (August 15, 1996) pp. 2234-2252.
EXAMINER	DATE CONSIDERED	
Cin 9-28	12/28/04	

FORM PTO - 1449		ATTY DOCKET NO.: ASC-025DVC1
INFORMATION DISCLOSURE STATEMENT		APPLICANTS: Cheng <i>et al.</i>
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OTHER ART, JOURNAL ARTICLES, ETC.		
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
CAF	C23	Fischetti, "Long-range Coulomb interactions in small Si devices. Part II. Effective electron mobility in thin-oxide structures," <u>Journal of Applied Physics</u> , Vol. 89, No. 2 (January 15, 2001) pp. 1232-1250.
CAF	C24	Fitzgerald et al., "Dislocation dynamics in relaxed graded composition semiconductors," <u>Materials Science and Engineering B67</u> (1999) pp. 53-61.
CAF	C25	Fitzgerald et al., "Relaxed Ge _x Si _{1-x} structures for III-V integration with Si and high mobility two-dimensional electron gases in Si," AT&T Bell Laboratories, Murray Hill, NJ 07974 (1992) <u>American Vacuum Society</u> , pp. 1807-1819.
CAF	C26	Fitzgerald et al., "Totally Relaxed Ge _x Si _{1-x} Layers with Low Threading Dislocation Densities Grown on Si Substrates," <u>Applied Physics Letters</u> , Vol. 59, No. 7 (August 12, 1991) pp. 811-813.
CAF	C27	Garone et al., "Silicon vapor phase epitaxial growth catalysis by the presence of germane," <u>Applied Physics Letters</u> , Vol. 56, No. 13 (March 26, 1990) pp. 1275-1277.
CAF	C28	Godbey et al., (1990) "Fabrication of Bond and Etch-Back Silicon Insulator Using a Strained Si _{0.7} Ge _{0.3} Layer as an Etch Stop," <u>Journal of the Electrical Society</u> , Vol. 137, No. 10 (October 1990) pp. 3219-3223.
CAF	C29	Gray and Meyer, "Phase-Locked Loops", <u>Analysis and Design of Analog Integrated Circuits</u> (1984) pp. 605-632.
CAF	C30	Grützmacher et al., "Ge segregation in SiGe/Si heterostructures and its dependence on deposition technique and growth atmosphere," <u>Applied Physics Letters</u> , Vol. 63, No. 18 (November 1, 1993) pp. 2531-2533.
CAF	C31	Hackbarth et al., "Alternatives to thick MBE-grown relaxed SiGe buffers," <u>Thin Solid Films</u> , Vol. 369, No. 1-2 (July 2000) pp. 148-151.
CAF	C32	Hackbarth et al., "Strain relieved SiGe buffers for Si-based heterostructure field-effect transistors," <u>Journal of Crystal Growth</u> , Vol. 201/202 (1999) pp. 734-738.
CAF	C33	Herzog et al., "SiGe-based FETs: buffer issues and device results," <u>Thin Solid Films</u> , Vol. 380 (2000) pp. 36-41.
CAF	C34	Höck et al., "Carrier mobilities in modulation doped Si _{1-x} Ge _x heterostructures with respect to FET applications," <u>Thin Solid Films</u> , Vol. 336 (1998) pp. 141-144.
CAF	C35	Höck et al., "High hole mobility in Si _{0.17} Ge _{0.83} channel metal-oxide-semiconductor field-effect transistors grown by plasma-enhanced chemical vapor deposition," <u>Applied Physics Letters</u> , Volume 76, No. 26 (June 26, 2000) pp. 3920-3922.
CAF	C36	Höck et al., "High performance 0.25 μ m p-type Ge/SiGe MODFETs," <u>Electronics Letters</u> , Vol. 34, No. 19 (September 17, 1998) pp. 1888-1889.
CAF	C37	Huang et al., (2001) "Carrier Mobility enhancement in strained Si-on-insulator fabricated by wafer bonding", <u>2001 Symposium on VLSI Technology, Digest of Technical Papers</u> , pages 57-58
CAF	C38	Huang et al., "High-quality strain-relaxed SiGe alloy grown on implanted silicon-on-insulator substrate," <u>Applied Physics Letters</u> , Vol. 76, No. 19 (May 8, 2000) pp. 2680-2682.
CAF	C39	Huang et al., "The Impact of Scaling Down to Deep Submicron on CMOS RF Circuits", <u>IEEE Journal of Solid-State Circuits</u> , Vol. 33, No. 7, July, 1998, pp. 1023-1036.
EXAMINER	DATE CONSIDERED	
Cia	12/28/04	

FORM PTO - 1449		ATTY DOCKET NO.: ASC-025DVC1
INFORMATION DISCLOSURE STATEMENT		APPLICANTS: Cheng <i>et al.</i>
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OTHER ART, JOURNAL ARTICLES, ETC.		
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
CAT	C40	IBM Technical Disclosure Bulletin, Volume 32, No. 8A, January 1990, "Optimal Growth Technique and Structure for Strain Relaxation of Si-Ge Layers on Si Substrates", pp. 330-331.
CAT	C41	Ishikawa et al., "Creation of Si-Ge-based SIMOX structures by low energy oxygen implantation," <u>Proceedings 1997 IEEE International SOI Conference</u> (October 1997) pp. 16-17.
CAT	C42	Ishikawa et al., "SiGe-on-insulator substrate using SiGe alloy grown Si(001)," <u>Applied Physics Letters</u> , Vol. 75, No. 7 (August 16, 1999) pp. 983-985.
CAT	C43	Ismail et al., "Modulation-doped n-type Si/SiGe with inverted interface," <u>Appl. Phys. Lett.</u> , Vol. 65, No. 10 (September 5, 1994) pp. 1248-1250.
CAT	C44	Ismail, "Si/SiGe High-Speed Field-Effect Transistors," <u>Electron Devices Meeting, Washington, D.C.</u> (December 10, 1995) pp. 20.1.1-20.1.4.
CAT	C45	Kearney et al., "The effect of alloy scattering on the mobility of holes in a Si _{1-x} Ge _x quantum well," <u>Semicond. Sci Technol.</u> , Vol. 13 (1998) pp. 174-180.
CAT	C46	Kim et al., "A Fully Integrated 1.9-GHz CMOS Low-Noise Amplifier," <u>IEEE Microwave and Guided Wave Letters</u> , Vol. 8, No. 8 (August 1998) pp. 293-295.
CAT	C47	Koester et al., "Extremely High Transconductance Ge/Si _{0.4} Ge _{0.6} p-MODFET's Grown by UHV-CVD," <u>IEEE Electron Device Letters</u> , Vol. 21, No. 3 (March 2000) pp. 110-112.
CAT	C48	König et al., "Design Rules for n-Type SiGe Hetero FETs," <u>Solid State Electronics</u> , Vol. 41, No. 10 (1997), pp. 1541-1547.
CAT	C49	König et al., "p-Type Ge-Channel MODFET's with High Transconductance Grown on Si Substrates," <u>IEEE Electron Device Letters</u> , Vol. 14, No. 4 (April 1993) pp. 205-207.
CAT	C50	König et al., "SiGe HBTs and HFETs," <u>Solid-State Electronics</u> , Vol. 38, No. 9 (1995) pp. 1595-1602.
CAT	C51	Kummer et al., "Low energy plasma enhanced chemical vapor deposition," <u>Materials Science and Engineering B89</u> (2002) pp. 288-295.
CAT	C52	Kuznetsov et al., "Technology for high-performance n-channel SiGe modulation-doped field-effect transistors," <u>J. Vac. Sci. Technol., B 13(6)</u> (November/December 1995) pp. 2892-2896.
CAT	C53	Langdo et al., (2002) "Preparation of Novel SiGe-free Strained Si on Insulator Substrates" <u>IEEE International SOI Conference</u> , pages 211-212 (XP002263057)
CAT	C54	Larson, "Integrated Circuit Technology Options for RFIC's - Present Status and Future Directions", <u>IEEE Journal of Solid-State Circuits</u> , Vol. 33, No. 3, March 1998, pp. 387-399.
CAT	C55	Lee et al., "CMOS RF Integrated Circuits at 5 GHz and Beyond", <u>Proceedings of the IEEE</u> , Vol. 88, No. 10 (October 2000) pp. 1560-1571.
CAT	C56	Lee et al., "Strained Ge channel p-type metal-oxide-semiconductor field-effect transistors grown on Si _{1-x} Ge _x /Si virtual substrates," <u>Applied Physics Letters</u> , Vol. 79, No. 20 (November 12, 2001) pp. 3344-3346.
CAT	C57	Lee et al., "Strained Ge channel p-type MOSFETs fabricated on Si _{1-x} Ge _x /Si virtual substrates," <u>Mat. Res. Soc. Symp. Proc.</u> , Vol. 686 (2002) pp. A1.9.1-A1.9.5.
EXAMINER <i>Cade</i>		DATE CONSIDERED 12/27/04

FORM PTO - 1449		ATTY DOCKET NO.: ASC-025DVC1
INFORMATION DISCLOSURE STATEMENT		APPLICANTS: Cheng <i>et al.</i>
		SERIAL NO.: 10/802,185
		FILING DATE: March 17, 2004
		GROUP: Not yet assigned 2813
OTHER ART, JOURNAL ARTICLES, ETC.		
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
CAT	C58	Leitz et al., "Channel Engineering of SiGe-Based Heterostructures for High Mobility MOSFETs," <u>Mat. Res. Soc. Symp. Proc.</u> , Vol. 686 (2002) pp. A3.10.1-A3.10.6.
CAT	C59	Leitz et al., "Dislocation glide and blocking kinetics in compositionally graded SiGe/Si," <u>Journal of Applied Physics</u> , Vol. 90, No. 6 (September 15, 2001) pp. 2730-2736.
CAT	C60	Leitz et al., "Hole mobility enhancements in strained Si/Si _{1-y} Ge _y p-type metal-oxide-semiconductor field-effect transistors grown on relaxed Si _{1-x} Ge _x (x<y) virtual substrates," <u>Applied Physics Letters</u> , Vol. 79, No. 25 (December 17, 2001) pp. 4246-4248.
CAT	C61	Li et al., "Design of high speed Si/SiGe heterojunction complementary metal-oxide-semiconductor field effect transistors with reduced short-channel effects," <u>J. Vac. Sci. Technol.</u> , Vol. 20 No.3 (May/June 2002) pp. 1030-1033.
CAT	C62	Lu et al., "High Performance 0.1 μ m Gate-Length P-Type SiGe MODFET's and MOS-MODFET's", <u>IEEE Transactions on Electron Devices</u> , Vol. 47, No. 8 (August 2000) pp. 1645-1652.
CAT	C63	Maiti et al., "Strained-Si heterostructure field effect transistors," <u>Semicond. Sci. Technol.</u> , Vol. 13 (1998) pp. 1225-1246.
CAT	C64	Maszara, "Silicon-On-Insulator by Wafer Bonding: A Review," <u>Journal of the Electrochemical Society</u> , No. 1 (January 1991) pp. 341-347.
CAT	C65	Meyerson et al., "Cooperative Growth Phenomena in Silicon/Germanium Low-Temperature Epitaxy," <u>Applied Physics Letters</u> , Vol. 53, No. 25 (December 19, 1988) pp. 2555-2557.
CAT	C66	Mizuno et al., "Advanced SOI-MOSFETs with Strained-Si Channel for High Speed CMOS-Electron/Hole Mobility Enhancement," 2000 Symposium on VLSI Technology, Digest of Technical Papers, Honolulu, (June 13-15), IEEE New York, NY, pp. 210-211.
CAT	C67	Mizuno et al., "Electron and Hole Mobility Enhancement in Strained-Si MOSFET's on SiGe-on-Insulator Substrates Fabricated by SIMOX Technology," <u>IEEE Electron Device Letters</u> , Vol. 21, No. 5 (May 2000) pp. 230-232.
CAT	C68	Mizuno et al., "High Performance Strained-Si p-MOSFETs on SiGe-on-Insulator Substrates Fabricated by SIMOX Technology," <u>IEEE IDEM Technical Digest</u> (1999) pp. 934-936.
CAT	C69	Nayak et al., "High-Mobility Strained-Si PMOSFET's", <u>IEEE Transactions on Electron Devices</u> , Vol. 43, No. 10 (October 1996) pp. 1709-1716.
CAT	C70	O'Neill et al., "SiGe Virtual substrate N-channel heterojunction MOSFETS," <u>Semicond. Sci. Technol.</u> , Vol. 14 (1999) pp. 784-789.
CAT	C71	Ota, Y. et al., "Application of heterojunction FET to power amplifier for cellular telephone," <u>Electronics Letters</u> , Vol. 30 No. 11 (May 26, 1994) pp. 906-907.
CAT	C72	Papananos, "Low Noise Amplifiers in MOS Technologies," and "Low Noise Tuned-LC Oscillator," <u>Radio-Frequency Microelectronic Circuits for Telecommunication Applications</u> (1999) pp. 115-117, 188-193.
CAT	C73	Parker et al., "SiGe heterostructure CMOS circuits and applications," <u>Solid State Electronics</u> , Vol. 43 (1999) pp. 1497-1506.
EXAMINER	DATE CONSIDERED 12/28/04	

FORM PTO - 1449		ATTY DOCKET NO.: ASC-025DVC1	
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<i>CAJ</i>	C74	Ransom et al., "Gate-Self-Aligned n-channel and p-channel Germanium MOSFET's," <u>IEEE Transactions on Electron Devices</u> , Vol. 38, No. 12 (December 1991) pp. 2695.	
<i>CAJ</i>	C75	Reinking et al., "Fabrication of high-mobility Ge p-channel MOSFETs on Si substrates," <u>Electronics Letters</u> , Vol. 35, No. 6 (March 18, 1999) pp. 503-504.	
<i>CAJ</i>	C76	Rim et al., "Enhanced Hole Mobilities in Surface-channel Strained-Si p-MOSFETs"; <u>IEDM</u> , 1995, pp. 517-520.	
<i>CAJ</i>	C77	Rim et al., "Fabrication and Analysis of Deep Submicron Strained-Si N-MOSFET's"; <u>IEEE Transactions on Electron Devices</u> , Vol. 47, No. 7 (July 2000) pp. 1406-1415.	
<i>CAJ</i>	C78	Rim, "Application of Silicon-Based Heterostructures to Enhanced Mobility Metal-Oxide-Semiconductor Field-Effect Transistors", Ph.D. Thesis, Stanford University (1999) pp. 1-184.	
<i>CAJ</i>	C79	Robbins et al., "A model for heterogeneous growth of Si _{1-x} Ge _x films for hydrides," <u>Journal of Applied Physics</u> , Vol. 69, No. 6 (March 15, 1991) pp. 3729-3732.	
<i>CAJ</i>	C80	Sadek et al., "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," <u>IEEE Trans. Electron Devices</u> (August 1996) pp. 1224-1232.	
<i>CAJ</i>	C81	Sakaguchi et al., "ELTRAN® by Splitting Porous Si Layers," Proc. 195 th Int. SOI Symposium, Vol. 99-3, <u>Electrochemical Society</u> (1999) pp. 117-121.	
<i>CAJ</i>	C82	Schäffler, "High-Mobility Si and Ge Structures," <u>Semiconductor Science and Technology</u> , Vol. 12 (1997) pp. 1515-1549.	
<i>CAJ</i>	C83	Sugimoto et al., "A 2V, 500 MHz and 3V, 920 MHz Low-Power Current-Mode 0.6 μ m CMOS VCO Circuit", <u>IEICE Trans. Electron.</u> , Vol.E82-C, No. 7 (July 1999) pp. 1327-1329.	
<i>CAJ</i>	C84	Tement et al., "Metal Gate Strained Silicon MOSFETs for Microwave Integrated Circuits", <u>IEEE</u> (October 2000) pp. 38-43.	
<i>CAJ</i>	C85	Tsang et al., "Measurements of alloy composition and strain in thin Ge _x Si _{1-x} layers," <u>J. Appl. Phys.</u> , Vol. 75 No. 12 (June 15, 1994) pp. 8098-8108.	
<i>CAJ</i>	C86	Tweet et al., "Factors determining the composition of strained GeSi layers grown with disilane and germane," <u>Applied Physics Letters</u> , Vol. 65, No. 20 (November 14, 1994) pp. 2579-2581.	
<i>CAJ</i>	C87	Usami et al., "Spectroscopic study of Si-based quantum wells with neighboring confinement structure," <u>Semicon. Sci. Technol.</u> (1997) (abstract).	
<i>CAJ</i>	C88	Welser et al., "Electron Mobility Enhancement in Strained-Si N-Type Metal-Oxide-Semiconductor Field-Effect Transistors," <u>IEEE Electron Device Letters</u> , Vol. 15, No. 3 (March 1994) pp. 100-102.	
<i>CAJ</i>	C89	Welser et al., "Evidence of Real-Space Hot-Electron Transfer in High Mobility, Strained-Si Multilayer MOSFETs," <u>IEEE IDEM Technical Digest</u> (1993) pp. 545-548.	
<i>CAJ</i>	C90	Welser et al., "NMOS and PMOS Transistors Fabricated in Strained Silicon/Relaxed Silicon-Germanium Structures," <u>IEEE IDEM Technical Digest</u> (1992) pp. 1000-1002.	
<i>CAJ</i>	C91	Welser, "The Application of Strained Silicon/Relaxed Silicon Germanium Heterostructures to Metal-Oxide-Semiconductor Field-Effect Transistors," Ph.D. Thesis, Stanford University (1994) pp. 1-205.	
<i>CAJ</i>	C92	Wolf et al., "Silicon Processing for the VLSI Era," Vol. 1 <u>Process Technology</u> (1986) pp. 384-386.	
EXAMINER <i>Craig A. [Signature]</i>		DATE CONSIDERED <i>12/28/04</i>	

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